Abstracts

Extraction of Low-Frequency Noise Model of Self-Aligned AlGaAs/GaAs Heterojunction Bipolar Transistor

J.-H. Shin, Y. Chung, Y. Suh and B. Kim. "Extraction of Low-Frequency Noise Model of Self-Aligned AlGaAs/GaAs Heterojunction Bipolar Transistor." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1309-1312.

The first quantitative extraction of low-frequency noise equivalent circuit model of self-aligned AlGaAs/GaAs heterojunction bipolar transistor has been performed. It is based on a generalized small signal circuit model including the base and emitter series resistance noise sources. The dominant noise sources are emitter-base current noise source and the resistance noise source. The emitter-collector current noise source is negligible.

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